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Intel - EPF10K50ETC144-3 Datasheet



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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	360
Number of Logic Elements/Cells	2880
Total RAM Bits	40960
Number of I/O	102
Number of Gates	199000
Voltage - Supply	2.3V ~ 2.7V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	144-LQFP
Supplier Device Package	144-TQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k50etc144-3

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Table 2. FLEX 10KE Device Features								
Feature	EPF10K100E (2)	EPF10K130E	EPF10K200E EPF10K200S					
Typical gates (1)	100,000	130,000	200,000					
Maximum system gates	257,000	342,000	513,000					
Logic elements (LEs)	4,992	6,656	9,984					
EABs	12	16	24					
Total RAM bits	49,152	65,536	98,304					
Maximum user I/O pins	338	413	470					

Note to tables:

- (1) The embedded IEEE Std. 1149.1 JTAG circuitry adds up to 31,250 gates in addition to the listed typical or maximum system gates.
- (2) New EPF10K100B designs should use EPF10K100E devices.

...and More

- Fabricated on an advanced process and operate with a 2.5-V internal supply voltage
- In-circuit reconfigurability (ICR) via external configuration devices, intelligent controller, or JTAG port
- ClockLock[™] and ClockBoost[™] options for reduced clock _ delay/skew and clock multiplication
- Built-in low-skew clock distribution trees
- 100% functional testing of all devices; test vectors or scan chains are not required
- Pull-up on I/O pins before and during configuration
- Flexible interconnect
 - FastTrack[®] Interconnect continuous routing structure for fast, predictable interconnect delays
 - Dedicated carry chain that implements arithmetic functions such as fast adders, counters, and comparators (automatically used by software tools and megafunctions)
 - Dedicated cascade chain that implements high-speed, high-fan-in logic functions (automatically used by software tools and megafunctions)
 - Tri-state emulation that implements internal tri-state buses
 - Up to six global clock signals and four global clear signals
 - Powerful I/O pins
 - Individual tri-state output enable control for each pin
 - Open-drain option on each I/O pin
 - Programmable output slew-rate control to reduce switching noise
 - Clamp to V_{CCIO} user-selectable on a pin-by-pin basis
 - Supports hot-socketing



Figure 4. FLEX 10KE Device in Single-Port RAM Mode

Note:

(1) EPF10K30E, EPF10K50E, and EPF10K50S devices have 88 EAB local interconnect channels; EPF10K100E, EPF10K130E, EPF10K200E, and EPF10K200S devices have 104 EAB local interconnect channels.

EABs can be used to implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the write enable signal. In contrast, the EAB's synchronous RAM generates its own write enable signal and is self-timed with respect to the input or write clock. A circuit using the EAB's self-timed RAM must only meet the setup and hold time specifications of the global clock. When used as RAM, each EAB can be configured in any of the following sizes: 256×16 , 512×8 , $1,024 \times 4$, or $2,048 \times 2$ (see Figure 5).



Larger blocks of RAM are created by combining multiple EABs. For example, two 256×16 RAM blocks can be combined to form a 256×32 block; two 512×8 RAM blocks can be combined to form a 512×16 block (see Figure 6).





If necessary, all EABs in a device can be cascaded to form a single RAM block. EABs can be cascaded to form RAM blocks of up to 2,048 words without impacting timing. The Altera software automatically combines EABs to meet a designer's RAM specifications.

Cascade Chain

With the cascade chain, the FLEX 10KE architecture can implement functions that have a very wide fan-in. Adjacent LUTs can be used to compute portions of the function in parallel; the cascade chain serially connects the intermediate values. The cascade chain can use a logical AND or logical OR (via De Morgan's inversion) to connect the outputs of adjacent LEs. An a delay as low as 0.6 ns per LE, each additional LE provides four more inputs to the effective width of a function. Cascade chain logic can be created automatically by the Altera Compiler during design processing, or manually by the designer during design entry.

Cascade chains longer than eight bits are implemented automatically by linking several LABs together. For easier routing, a long cascade chain skips every other LAB in a row. A cascade chain longer than one LAB skips either from even-numbered LAB to even-numbered LAB, or from odd-numbered LAB to odd-numbered LAB (e.g., the last LE of the first LAB in a row cascades to the first LE of the third LAB). The cascade chain does not cross the center of the row (e.g., in the EPF10K50E device, the cascade chain stops at the eighteenth LAB and a new one begins at the nineteenth LAB). This break is due to the EAB's placement in the middle of the row.

Figure 10 shows how the cascade function can connect adjacent LEs to form functions with a wide fan-in. These examples show functions of 4n variables implemented with n LEs. The LE delay is 0.9 ns; the cascade chain delay is 0.6 ns. With the cascade chain, 2.7 ns are needed to decode a 16-bit address.



Figure 10. FLEX 10KE Cascade Chain Operation

Altera Corporation

FastTrack Interconnect Routing Structure

In the FLEX 10KE architecture, connections between LEs, EABs, and device I/O pins are provided by the FastTrack Interconnect routing structure, which is a series of continuous horizontal and vertical routing channels that traverses the device. This global routing structure provides predictable performance, even in complex designs. In contrast, the segmented routing in FPGAs requires switch matrices to connect a variable number of routing paths, increasing the delays between logic resources and reducing performance.

The FastTrack Interconnect routing structure consists of row and column interconnect channels that span the entire device. Each row of LABs is served by a dedicated row interconnect. The row interconnect can drive I/O pins and feed other LABs in the row. The column interconnect routes signals between rows and can drive I/O pins.

Row channels drive into the LAB or EAB local interconnect. The row signal is buffered at every LAB or EAB to reduce the effect of fan-out on delay. A row channel can be driven by an LE or by one of three column channels. These four signals feed dual 4-to-1 multiplexers that connect to two specific row channels. These multiplexers, which are connected to each LE, allow column channels to drive row channels even when all eight LEs in a LAB drive the row interconnect.

Each column of LABs or EABs is served by a dedicated column interconnect. The column interconnect that serves the EABs has twice as many channels as other column interconnects. The column interconnect can then drive I/O pins or another row's interconnect to route the signals to other LABs or EABs in the device. A signal from the column interconnect, which can be either the output of a LE or an input from an I/O pin, must be routed to the row interconnect before it can enter a LAB or EAB. Each row channel that is driven by an IOE or EAB can drive one specific column channel.

Access to row and column channels can be switched between LEs in adjacent pairs of LABs. For example, a LE in one LAB can drive the row and column channels normally driven by a particular LE in the adjacent LAB in the same row, and vice versa. This flexibility enables routing resources to be used more efficiently (see Figure 13).

Table 9. Peripheral Bus Sources for EPF10K100E, EPF10K130E, EPF10K200E & EPF10K200S Devices									
Peripheral Control Signal	EPF10K100E	EPF10K130E	EPF10K200E EPF10K200S						
OE 0	Row A	Row C	Row G						
OE1	Row C	Row E	Row I						
OE 2	Row E	Row G	Row K						
OE 3	Row L	Row N	Row R						
OE4	Row I	Row K	Row O						
OE5	Row K	Row M	Row Q						
CLKENA0/CLK0/GLOBAL0	Row F	Row H	Row L						
CLKENA1/OE6/GLOBAL1	Row D	Row F	Row J						
CLKENA2/CLR0	Row B	Row D	Row H						
CLKENA3/OE7/GLOBAL2	Row H	Row J	Row N						
CLKENA4/CLR1	Row J	Row L	Row P						
CLKENA5/CLK1/GLOBAL3	Row G	Row I	Row M						

Signals on the peripheral control bus can also drive the four global signals, referred to as GLOBAL0 through GLOBAL3 in Tables 8 and 9. An internally generated signal can drive a global signal, providing the same low-skew, low-delay characteristics as a signal driven by an input pin. An LE drives the global signal by driving a row line that drives the peripheral bus, which then drives the global signal. This feature is ideal for internally generated clear or clock signals with high fan-out. However, internally driven global signals offer no advantage over the general-purpose interconnect for routing data signals. The dedicated input pin should be driven to a known logic state (such as ground) and not be allowed to float.

The chip-wide output enable pin is an active-high pin (DEV_OE) that can be used to tri-state all pins on the device. This option can be set in the Altera software. On EPF10K50E and EPF10K200E devices, the built-in I/O pin pull-up resistors (which are active during configuration) are active when the chip-wide output enable pin is asserted. The registers in the IOE can also be reset by the chip-wide reset pin.

ClockLock & ClockBoost Timing Parameters

For the ClockLock and ClockBoost circuitry to function properly, the incoming clock must meet certain requirements. If these specifications are not met, the circuitry may not lock onto the incoming clock, which generates an erroneous clock within the device. The clock generated by the ClockLock and ClockBoost circuitry must also meet certain specifications. If the incoming clock meets these requirements during configuration, the ClockLock and ClockBoost circuitry will lock onto the clock during configuration. The circuit will be ready for use immediately after configuration. Figure 19 shows the incoming and generated clock specifications.

Figure 19. Specifications for Incoming & Generated Clocks

The t_l parameter refers to the nominal input clock period; the t_0 parameter refers to the nominal output clock period.



The VCCINT pins must always be connected to a 2.5-V power supply. With a 2.5-V V_{CCINT} level, input voltages are compatible with 2.5-V, 3.3-V, and 5.0-V inputs. The VCCIO pins can be connected to either a 2.5-V or 3.3-V power supply, depending on the output requirements. When the VCCIO pins are connected to a 2.5-V power supply, the output levels are compatible with 2.5-V systems. When the VCCIO pins are connected to a 3.3-V power supply, the output high is at 3.3 V and is therefore compatible with 3.3-V or 5.0-V systems. Devices operating with V_{CCIO} levels higher than 3.0 V achieve a faster timing delay of t_{OD2} instead of t_{OD1} .

Table 14. FLEX 10KE MultiVolt I/O Support								
V _{CCIO} (V)	Inp	out Signal	(V)	Out	out Signal	(V)		
	2.5	3.3	5.0	2.5	3.3	5.0		
2.5	~	✓(1)	✓ (1)	~				
3.3	\checkmark	\checkmark	✓ (1)	✓(2)	\checkmark	~		

Table 14 summarizes FLEX 10KE MultiVolt I/O support.

Notes:

(1) The PCI clamping diode must be disabled to drive an input with voltages higher than $V_{\rm CCIO}$.

(2) When V_{CCIO} = 3.3 V, a FLEX 10KE device can drive a 2.5-V device that has 3.3-V tolerant inputs.

Open-drain output pins on FLEX 10KE devices (with a pull-up resistor to the 5.0-V supply) can drive 5.0-V CMOS input pins that require a $V_{\rm IH}$ of 3.5 V. When the open-drain pin is active, it will drive low. When the pin is inactive, the trace will be pulled up to 5.0 V by the resistor. The open-drain pin will only drive low or tri-state; it will never drive high. The rise time is dependent on the value of the pull-up resistor and load impedance. The I_{OL} current specification should be considered when selecting a pull-up resistor.

Power Sequencing & Hot-Socketing

Because FLEX 10KE devices can be used in a mixed-voltage environment, they have been designed specifically to tolerate any possible power-up sequence. The $V_{\rm CCIO}$ and $V_{\rm CCINT}$ power planes can be powered in any order.

Signals can be driven into FLEX 10KE devices before and during power up without damaging the device. Additionally, FLEX 10KE devices do not drive out during power up. Once operating conditions are reached, FLEX 10KE devices operate as specified by the user.

IEEE Std. 1149.1 (JTAG) Boundary-Scan Support

All FLEX 10KE devices provide JTAG BST circuitry that complies with the IEEE Std. 1149.1-1990 specification. FLEX 10KE devices can also be configured using the JTAG pins through the BitBlaster or ByteBlasterMV download cable, or via hardware that uses the Jam[™] STAPL programming and test language. JTAG boundary-scan testing can be performed before or after configuration, but not during configuration. FLEX 10KE devices support the JTAG instructions shown in Table 15.

Table 15. FLEX 10KE JTAG Instructions						
JTAG Instruction	Description					
SAMPLE/PRELOAD	Allows a snapshot of signals at the device pins to be captured and examined during normal device operation, and permits an initial data pattern to be output at the device pins.					
EXTEST	Allows the external circuitry and board-level interconnections to be tested by forcing a test pattern at the output pins and capturing test results at the input pins.					
BYPASS	Places the 1-bit bypass register between the TDI and TDO pins, which allows the BST data to pass synchronously through a selected device to adjacent devices during normal device operation.					
USERCODE	Selects the user electronic signature (USERCODE) register and places it between the TDI and TDO pins, allowing the USERCODE to be serially shifted out of TDO.					
IDCODE	Selects the IDCODE register and places it between TDI and TDO, allowing the IDCODE to be serially shifted out of TDO.					
ICR Instructions	These instructions are used when configuring a FLEX 10KE device via JTAG ports with a BitBlaster or ByteBlasterMV download cable, or using a Jam File (.jam) or Jam Byte-Code File (.jbc) via an embedded processor.					

The instruction register length of FLEX 10KE devices is 10 bits. The USERCODE register length in FLEX 10KE devices is 32 bits; 7 bits are determined by the user, and 25 bits are pre-determined. Tables 16 and 17 show the boundary-scan register length and device IDCODE information for FLEX 10KE devices.

Table 16. FLEX 10KE Boundary-Scan Register Length							
Device	Boundary-Scan Register Length						
EPF10K30E	690						
EPF10K50E	798						
EPF10K50S							
EPF10K100E	1,050						
EPF10K130E	1,308						
EPF10K200E	1,446						
EPF10K200S							

Table 22	Table 22. FLEX 10KE 2.5-V Device DC Operating Conditions Notes (6), (7)									
Symbol	Parameter	Conditions	Min	Тур	Max	Unit				
V _{IH}	High-level input voltage		$1.7, 0.5 \times V_{CCIO}$ (8)		5.75	V				
V _{IL}	Low-level input voltage		-0.5		0.8, 0.3 × V _{CCIO} <i>(8)</i>	V				
V _{OH}	3.3-V high-level TTL output voltage	I _{OH} = -8 mA DC, V _{CCIO} = 3.00 V <i>(</i> 9 <i>)</i>	2.4			V				
	3.3-V high-level CMOS output voltage	I _{OH} = -0.1 mA DC, V _{CCIO} = 3.00 V <i>(</i> 9 <i>)</i>	V _{CCIO} – 0.2			V				
	3.3-V high-level PCI output voltage	$I_{OH} = -0.5 \text{ mA DC},$ $V_{CCIO} = 3.00 \text{ to } 3.60 \text{ V} (9)$	$0.9 imes V_{CCIO}$			V				
	2.5-V high-level output voltage	I _{OH} = -0.1 mA DC, V _{CCIO} = 2.30 V <i>(</i> 9 <i>)</i>	2.1			V				
		I _{OH} = -1 mA DC, V _{CCIO} = 2.30 V <i>(9)</i>	2.0			V				
		$I_{OH} = -2 \text{ mA DC},$ $V_{CCIO} = 2.30 \text{ V} (9)$	1.7			V				
V _{OL}	3.3-V low-level TTL output voltage	I _{OL} = 12 mA DC, V _{CCIO} = 3.00 V (10)			0.45	V				
	3.3-V low-level CMOS output voltage	I _{OL} = 0.1 mA DC, V _{CCIO} = 3.00 V (10)			0.2	V				
	3.3-V low-level PCI output voltage	I_{OL} = 1.5 mA DC, V _{CCIO} = 3.00 to 3.60 V (10)			$0.1 \times V_{CCIO}$	V				
	2.5-V low-level output voltage	$I_{OL} = 0.1 \text{ mA DC},$ $V_{CCIO} = 2.30 \text{ V} (10)$			0.2	V				
		I _{OL} = 1 mA DC, V _{CCIO} = 2.30 V (10)			0.4	V				
		I _{OL} = 2 mA DC, V _{CCIO} = 2.30 V (10)			0.7	V				
I _I	Input pin leakage current	$V_{I} = V_{CCIOmax}$ to 0 V (11)	-10		10	μA				
I _{OZ}	Tri-stated I/O pin leakage current	$V_{O} = V_{CCIOmax}$ to 0 V (11)	-10		10	μA				
I _{CC0}	V _{CC} supply current (standby)	V _I = ground, no load, no toggling inputs		5		mA				
		V _I = ground, no load, no toggling inputs <i>(12)</i>		10		mA				
R _{CONF}	Value of I/O pin pull-	V _{CCIO} = 3.0 V (13)	20		50	k¾				
	up resistor before and during configuration	$V_{CCIO} = 2.3 V (13)$	30		80	k¾				





Figure 23. Output Drive Characteristics of FLEX 10KE Devices Note (1)

Note:

(1) These are transient (AC) currents.

Timing Model

The continuous, high-performance FastTrack Interconnect routing resources ensure predictable performance and accurate simulation and timing analysis. This predictable performance contrasts with that of FPGAs, which use a segmented connection scheme and therefore have unpredictable performance.

Device performance can be estimated by following the signal path from a source, through the interconnect, to the destination. For example, the registered performance between two LEs on the same row can be calculated by adding the following parameters:

- LE register clock-to-output delay (*t*_{CO})
- Interconnect delay (t_{SAMEROW})
- **LE** look-up table delay (t_{LUT})
- **LE** register setup time (t_{SU})

The routing delay depends on the placement of the source and destination LEs. A more complex registered path may involve multiple combinatorial LEs between the source and destination LEs.

Figure 30. EAB Synchronous Timing Waveforms

EAB Synchronous Write (EAB Output Registers Used)

Tables 31 through 37 show EPF10K30E device internal and external timing parameters.

Table 31. EPF10K30E Device LE Timing Microparameters (Part 1 of 2) Note (1)									
Symbol -1 Spe		ed Grade -2 Spe		ed Grade -3 Sp		d Grade	Unit		
	Min	Max	Min	Max	Min	Max			
t _{LUT}		0.7		0.8		1.1	ns		
t _{CLUT}		0.5		0.6		0.8	ns		
t _{RLUT}		0.6		0.7		1.0	ns		
t _{PACKED}		0.3		0.4		0.5	ns		
t _{EN}		0.6		0.8		1.0	ns		
t _{CICO}		0.1		0.1		0.2	ns		
t _{CGEN}		0.4		0.5		0.7	ns		

Table 35. EPF10K30E Device Interconnect Timing Microparameters Note (1)								
Symbol	-1 Spee	d Grade	-2 Spee	d Grade	-3 Spee	ed Grade	Unit	
	Min	Max	Min	Max	Min	Max		
t _{DIN2IOE}		1.8		2.4		2.9	ns	
t _{DIN2LE}		1.5		1.8		2.4	ns	
t _{DIN2DATA}		1.5		1.8		2.2	ns	
t _{DCLK2IOE}		2.2		2.6		3.0	ns	
t _{DCLK2LE}		1.5		1.8		2.4	ns	
t _{SAMELAB}		0.1		0.2		0.3	ns	
t _{SAMEROW}		2.0		2.4		2.7	ns	
t _{SAMECOLUMN}		0.7		1.0		0.8	ns	
t _{DIFFROW}		2.7		3.4		3.5	ns	
t _{TWOROWS}		4.7		5.8		6.2	ns	
t _{LEPERIPH}		2.7		3.4		3.8	ns	
t _{LABCARRY}		0.3		0.4		0.5	ns	
t _{LABCASC}		0.8		0.8		1.1	ns	

Table 36. EPF10K30E External Timing Parameters Notes (1), (2)								
Symbol	-1 Speed Grade		-2 Spee	-2 Speed Grade		ed Grade	Unit	
	Min	Max	Min	Max	Min	Max		
t _{DRR}		8.0		9.5		12.5	ns	
t _{INSU} (3)	2.1		2.5		3.9		ns	
t _{INH} (3)	0.0		0.0		0.0		ns	
t _{оитсо} (3)	2.0	4.9	2.0	5.9	2.0	7.6	ns	
t _{INSU} (4)	1.1		1.5		-		ns	
t _{INH} (4)	0.0		0.0		-		ns	
t _{оитсо} (4)	0.5	3.9	0.5	4.9	-	-	ns	
t _{PCISU}	3.0		4.2		-		ns	
t _{PCIH}	0.0		0.0		-		ns	
t _{PCICO}	2.0	6.0	2.0	7.5	-	-	ns	

Table 40. EPF10K50E Device EAB Internal Microparameters Note (1)							
Symbol	-1 Spee	ed Grade	-2 Spee	ed Grade	-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{EABDATA1}		1.7		2.0		2.7	ns
t _{EABDATA1}		0.6		0.7		0.9	ns
t _{EABWE1}		1.1		1.3		1.8	ns
t _{EABWE2}		0.4		0.4		0.6	ns
t _{EABRE1}		0.8		0.9		1.2	ns
t _{EABRE2}		0.4		0.4		0.6	ns
t _{EABCLK}		0.0		0.0		0.0	ns
t _{EABCO}		0.3		0.3		0.5	ns
t _{EABBYPASS}		0.5		0.6		0.8	ns
t _{EABSU}	0.9		1.0		1.4		ns
t _{EABH}	0.4		0.4		0.6		ns
t _{EABCLR}	0.3		0.3		0.5		ns
t _{AA}		3.2		3.8		5.1	ns
t _{WP}	2.5		2.9		3.9		ns
t _{RP}	0.9		1.1		1.5		ns
t _{WDSU}	0.9		1.0		1.4		ns
t _{WDH}	0.1		0.1		0.2		ns
t _{WASU}	1.7		2.0		2.7		ns
t _{WAH}	1.8		2.1		2.9		ns
t _{RASU}	3.1		3.7		5.0		ns
t _{RAH}	0.2		0.2		0.3		ns
t _{WO}		2.5		2.9		3.9	ns
t _{DD}		2.5		2.9		3.9	ns
t _{EABOUT}		0.5		0.6		0.8	ns
t _{EABCH}	1.5		2.0		2.5		ns
t _{EABCL}	2.5		2.9		3.9		ns

Table 50. EPF10K100E External Timing Parameters Notes (1), (2)								
Symbol	-1 Spee	d Grade	-2 Spee	-2 Speed Grade		d Grade	Unit	
	Min	Max	Min	Max	Min	Max		
t _{DRR}		9.0		12.0		16.0	ns	
t _{INSU} (3)	2.0		2.5		3.3		ns	
t _{INH} (3)	0.0		0.0		0.0		ns	
t _{оитсо} (3)	2.0	5.2	2.0	6.9	2.0	9.1	ns	
t _{INSU} (4)	2.0		2.2		-		ns	
t _{INH} (4)	0.0		0.0		-		ns	
t _{оитсо} (4)	0.5	3.0	0.5	4.6	-	-	ns	
t _{PCISU}	3.0		6.2		-		ns	
t _{PCIH}	0.0		0.0		-		ns	
t _{PCICO}	2.0	6.0	2.0	6.9	_	_	ns	

 Table 51. EPF10K100E External Bidirectional Timing Parameters
 Notes (1), (2)

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{INSUBIDIR} (3)	1.7		2.5		3.3		ns
t _{INHBIDIR} (3)	0.0		0.0		0.0		ns
t _{INSUBIDIR} (4)	2.0		2.8		-		ns
t _{INHBIDIR} (4)	0.0		0.0		-		ns
t _{OUTCOBIDIR} (3)	2.0	5.2	2.0	6.9	2.0	9.1	ns
t _{XZBIDIR} (3)		5.6		7.5		10.1	ns
t _{ZXBIDIR} (3)		5.6		7.5		10.1	ns
t _{OUTCOBIDIR} (4)	0.5	3.0	0.5	4.6	-	-	ns
t _{XZBIDIR} (4)		4.6		6.5		-	ns
t _{ZXBIDIR} (4)		4.6		6.5		-	ns

Notes to tables:

(1) All timing parameters are described in Tables 24 through 30 in this data sheet.

(2) These parameters are specified by characterization.

(3) This parameter is measured without the use of the ClockLock or ClockBoost circuits.

(4) This parameter is measured with the use of the ClockLock or ClockBoost circuits.

Table 56. EPF10K130E Device Interconnect Timing Microparameters Note (1)							
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{DIN2IOE}		2.8		3.5		4.4	ns
t _{DIN2LE}		0.7		1.2		1.6	ns
t _{DIN2DATA}		1.6		1.9		2.2	ns
t _{DCLK2IOE}		1.6		2.1		2.7	ns
t _{DCLK2LE}		0.7		1.2		1.6	ns
t _{SAMELAB}		0.1		0.2		0.2	ns
t _{SAMEROW}		1.9		3.4		5.1	ns
t _{SAMECOLUMN}		0.9		2.6		4.4	ns
t _{DIFFROW}		2.8		6.0		9.5	ns
t _{TWOROWS}		4.7		9.4		14.6	ns
t _{LEPERIPH}		3.1		4.7		6.9	ns
t _{LABCARRY}		0.6		0.8		1.0	ns
t _{LABCASC}		0.9		1.2		1.6	ns

Table 57. EPF10K130E External Timing Parameters Notes (1), (2)							
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{DRR}		9.0		12.0		16.0	ns
t _{INSU} (3)	1.9		2.1		3.0		ns
t _{INH} (3)	0.0		0.0		0.0		ns
t _{оитсо} (3)	2.0	5.0	2.0	7.0	2.0	9.2	ns
t _{INSU} (4)	0.9		1.1		-		ns
t _{INH} (4)	0.0		0.0		-		ns
t _{OUTCO} (4)	0.5	4.0	0.5	6.0	-	-	ns
t _{PCISU}	3.0		6.2		-		ns
t _{PCIH}	0.0		0.0		-		ns
t _{PCICO}	2.0	6.0	2.0	6.9	-	-	ns

Table 73. EPF10K200S Device Internal & External Timing Parameters Note (1)							
Symbol	Symbol -1 Speed Grad		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{LUT}		0.7		0.8		1.2	ns
t _{CLUT}		0.4		0.5		0.6	ns
t _{RLUT}		0.5		0.7		0.9	ns
t _{PACKED}		0.4		0.5		0.7	ns
t _{EN}		0.6		0.5		0.6	ns
t _{CICO}		0.1		0.2		0.3	ns
t _{CGEN}		0.3		0.4		0.6	ns
t _{CGENR}		0.1		0.2		0.3	ns
t _{CASC}		0.7		0.8		1.2	ns
t _C		0.5		0.6		0.8	ns
t _{CO}		0.5		0.6		0.8	ns
t _{COMB}		0.3		0.6		0.8	ns
t _{SU}	0.4		0.6		0.7		ns
t _H	1.0		1.1		1.5		ns
t _{PRE}		0.4		0.6		0.8	ns
t _{CLR}		0.5		0.6		0.8	ns
t _{CH}	2.0		2.5		3.0		ns
t _{CL}	2.0		2.5		3.0		ns

 Table 74. EPF10K200S Device IOE Timing Microparameters (Part 1 of 2)
 Note (1)

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{IOD}		1.8		1.9		2.6	ns
t _{IOC}		0.3		0.3		0.5	ns
t _{IOCO}		1.7		1.9		2.6	ns
t _{IOCOMB}		0.5		0.6		0.8	ns
t _{IOSU}	0.8		0.9		1.2		ns
t _{IOH}	0.4		0.8		1.1		ns
t _{IOCLR}		0.2		0.2		0.3	ns
t _{OD1}		1.3		0.7		0.9	ns
t _{OD2}		0.8		0.2		0.4	ns
t _{OD3}		2.9		3.0		3.9	ns
t _{XZ}		5.0		5.3		7.1	ns
t _{ZX1}		5.0		5.3		7.1	ns

To better reflect actual designs, the power model (and the constant K in the power calculation equations) for continuous interconnect FLEX devices assumes that LEs drive FastTrack Interconnect channels. In contrast, the power model of segmented FPGAs assumes that all LEs drive only one short interconnect segment. This assumption may lead to inaccurate results when compared to measured power consumption for actual designs in segmented FPGAs.

Figure 31 shows the relationship between the current and operating frequency of FLEX 10KE devices.

Figure 31. FLEX 10KE I_{CCACTIVE} vs. Operating Frequency (Part 1 of 2)

During initialization, which occurs immediately after configuration, the device resets registers, enables I/O pins, and begins to operate as a logic device. The I/O pins are tri-stated during power-up, and before and during configuration. Together, the configuration and initialization processes are called *command mode*; normal device operation is called *user mode*.

SRAM configuration elements allow FLEX 10KE devices to be reconfigured in-circuit by loading new configuration data into the device. Real-time reconfiguration is performed by forcing the device into command mode with a device pin, loading different configuration data, reinitializing the device, and resuming user-mode operation. The entire reconfiguration process requires less than 85 ms and can be used to reconfigure an entire system dynamically. In-field upgrades can be performed by distributing new configuration files.

Before and during configuration, all I/O pins (except dedicated inputs, clock, or configuration pins) are pulled high by a weak pull-up resistor.

Programming Files

Despite being function- and pin-compatible, FLEX 10KE devices are not programming- or configuration file-compatible with FLEX 10K or FLEX 10KA devices. A design therefore must be recompiled before it is transferred from a FLEX 10K or FLEX 10KA device to an equivalent FLEX 10KE device. This recompilation should be performed both to create a new programming or configuration file and to check design timing in FLEX 10KE devices, which has different timing characteristics than FLEX 10K or FLEX 10KA devices.

FLEX 10KE devices are generally pin-compatible with equivalent FLEX 10KA devices. In some cases, FLEX 10KE devices have fewer I/O pins than the equivalent FLEX 10KA devices. Table 81 shows which FLEX 10KE devices have fewer I/O pins than equivalent FLEX 10KA devices. However, power, ground, JTAG, and configuration pins are the same on FLEX 10KA and FLEX 10KE devices, enabling migration from a FLEX 10KA design to a FLEX 10KE design. Additionally, the Altera software offers several features that help plan for future device migration by preventing the use of conflicting I/O pins.

Table 81. I/O Counts for FLEX 10KA & FLEX 10KE Devices						
FLEX 10	KA	FLEX 10KE				
Device	I/O Count	Device	I/O Count			
EPF10K30AF256	191	EPF10K30EF256	176			
EPF10K30AF484	246	EPF10K30EF484	220			
EPF10K50VB356	274	EPF10K50SB356	220			
EPF10K50VF484	291	EPF10K50EF484	254			
EPF10K50VF484	291	EPF10K50SF484	254			
EPF10K100AF484	369	EPF10K100EF484	338			

Configuration Schemes

The configuration data for a FLEX 10KE device can be loaded with one of five configuration schemes (see Table 82), chosen on the basis of the target application. An EPC1, EPC2, or EPC16 configuration device, intelligent controller, or the JTAG port can be used to control the configuration of a FLEX 10KE device, allowing automatic configuration on system power-up.

Multiple FLEX 10KE devices can be configured in any of the five configuration schemes by connecting the configuration enable (nCE) and configuration enable output (nCEO) pins on each device. Additional FLEX 10K, FLEX 10KA, FLEX 10KE, and FLEX 6000 devices can be configured in the same serial chain.

Table 82. Data Sources for FLEX 10KE Configuration				
Configuration Scheme	Data Source			
Configuration device	EPC1, EPC2, or EPC16 configuration device			
Passive serial (PS)	BitBlaster, ByteBlasterMV, or MasterBlaster download cables, or serial data source			
Passive parallel asynchronous (PPA)	Parallel data source			
Passive parallel synchronous (PPS)	Parallel data source			
JTAG	BitBlaster or ByteBlasterMV download cables, or microprocessor with a Jam STAPL file or JBC file			